

Application Number: 13/723,046 (Parent et al) At Docket 2911 Assignment: continued 2-ct18

CLAIMS: Please amend the claims according to the status designations in the following list which contains all claims that were ever in the parent application, with the sum of all active claims.

What claim set:

1. (Currently amended) A semiconductor device, comprising
a substrate with texture on the top surface of said substrate, and
an epitaxial layer comprising an active layer and grown on the top of said texture.
2. (Original) The semiconductor device of claim 1, further comprising buffer layer grown
in between said epitaxial layer and said texture.
3. (Original) The semiconductor device of claim 1, wherein said texture comprising wells
and wells.
4. (Original) The semiconductor device of claim 3, wherein the width of said walls is in a
range of nanometers to micrometers.
5. (Original) The semiconductor device of claim 3, wherein the depth of said well is in a
range of nanometers to micrometers.
6. (Currently amended) The semiconductor device of claim 3, wherein said walls having a
shape of trapezoid.
7. (Original) The semiconductor device of claim 6, wherein the dimension of said walls is in
the range of nanometers to micrometers.
8. (currently amended) The semiconductor device of claim 1, wherein said epitaxial layer of
said semiconductor device exists right.
9. [Deletion] A semiconductor device, comprising

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- 3 substrate with first texture on one of its two surfaces;
- 4 first epitaxial layer comprising first active layer and grown on the top of said first texture;
- 5 second texture etched on the top surface of said first epitaxial layer;
- 6 second epitaxial layer comprising second active layer and grown on the top of said first texture;
- 7 record texture.
- 8 [Deletion] The semiconductor device of claim 9, further comprising first buffer layer grown in between said first epitaxial layer and said first texture of said substrate, and a second buffer layer grown in between said second epitaxial layer and said second texture of said first epitaxial layer.
- 9 [Deletion] The semiconductor device of claim 9, wherein both said first texture and said second texture comprising wells and walls.
- 10 [Deletion] The semiconductor device of claim 11, wherein the width of said walls is in a range of nanometers to micrometers.
- 11 [Deletion] The semiconductor device of claim 11, wherein the depth of said wells is in a range of nanometers to micrometers.
- 12 [Deletion] The semiconductor device of claim 11, wherein said wells have the shape of said semiconductor device.
- 13 [Deletion] The semiconductor device of claim 11, wherein said wells have the shape of said semiconductor device.
- 14 [Deletion] The semiconductor device of claim 11, wherein the dimension of said wells is in the range of nanometers to micrometers.
- 15 [Deletion] The semiconductor device of claim 11, wherein the dimension of said wells is in the range of nanometers to micrometers.
- 16 [Deletion] The semiconductor device of claim 9, wherein said substrate emits light.